Lawrence Berkeley National Laboratory

Recent Work

Title

A PREAMPLIFIER WITH 0.7 keV RESOLUTION FOR SEMICONDUCTOR RADIATION DETECTORS

Permalink

https://escholarship.org/uc/item/41f1465p

Author

Elad, Emanuel.

Publication Date

1965-09-07

University of California

Ernest O. Lawrence Radiation Laboratory

TWO-WEEK LOAN COPY

This is a Library Circulating Copy which may be borrowed for two weeks. For a personal retention copy, call Tech. Info. Division, Ext. 5545

A PREAMPLIFIER WITH 0.7 keV RESOLUTION FOR SEMICONDUCTOR RADIATION DETECTORS

Berkeley, California

DISCLAIMER

This document was prepared as an account of work sponsored by the United States Government. While this document is believed to contain correct information, neither the United States Government nor any agency thereof, nor the Regents of the University of California, nor any of their employees, makes any warranty, express or implied, or assumes any legal responsibility for the accuracy, completeness, or usefulness of any information, apparatus, product, or process disclosed, or represents that its use would not infringe privately owned rights. Reference herein to any specific commercial product, process, or service by its trade name, trademark, manufacturer, or otherwise, does not necessarily constitute or imply its endorsement, recommendation, or favoring by the United States Government or any agency thereof, or the Regents of the University of California. The views and opinions of authors expressed herein do not necessarily state or reflect those of the United States Government or any agency thereof or the Regents of the University of California.

UNIVERSITY OF CALIFORNIA

Lawrence Radiation Laboratory Berkeley, California

AEC Contract No. W-7405-eng-48

A PREAMPLIFIER WITH 0.7 keV RESOLUTION FOR SEMICONDUCTOR RADIATION DETECTORS

Emanuel Elad

September 7, 1965

A PREAMPLIFIER WITH 0.7 keV RESOLUTION FOR SEMICONDUCTOR RADIATION DETECTORS

Emanuel Elad

Lawrence Radiation Laboratory
University of California
Berkeley, California

September 7, 1965

The inherent low noise of the field-effect transistor (FET) made it an attractive candidate for the input stage of high resolution preamplifiers. Recently, a number of preamplifier circuits using an FET in the input stage have been published. 1,2,3 This letter describes briefly a low-noise FET preamplifier (pulse generator resolution 0.7 keV FWHM) with which 1.1 keV resolution was achieved in measurement of γ -ray spectra of 57 Co. The approach followed in the design of the described preamplifier was based on the optimization of the signal-to-noise ratio. The following steps were taken to achieve this purpose:

- a. The input stage was inserted into the chamber containing the detector.
- b. The input stage was simplified by insulating the detector from ground.
- c. The FET was cooled to improve its signal-to-noise performance.
- d. High frequency filters were used inside the charge-sensitive amplifier,
- e. Careful layout was made for the input stage and the following sections.
- f. A special low-capacitance and low-leakage lithium-drifted germanium detector was used.

The block diagram of the preamplifier is given in Fig. 1. The detector used is a LRL-Livermore-type lithium-drifted germanium diode with dimensions $3\times1\times0.3$ cm and capacitance of 1.9 pF. ⁴ The bias voltages used for this type of detector are in the range of 700 to 1500 V, and the leakage currents

range from 0.5 to 3 nA. This low leakage is obtained keeping the detector cooled to liquid nitrogen temperature in vacuum of 2×10^{-7} mm Hg.

The charge signal delivered by the detector is applied to a charge-sensitive amplifier composed of common-source FET stage, an integrator and amplifier 1. The capacitive negative feedback of this high-gain configuration ensures its charge sensitivity and the stability of output signal with changes of the detector's capacitance.

As mentioned before, the FET stage was mounted inside the chamber containing the detector. The following advantages were gained by this mounting:

- (a) Input stray capacitance is minimized by bringing the FET as close as possible to the detector and eliminating the capacitance of the feed-through terminals.
- (b) The cooling of the field-effect transistor is simplified.
- (c) The inherent shielding of the input stage by the metal chamber containing the detector is very effective in eliminating the low-frequency noise which might otherwise saturate the preamplifier.

The complete circuit diagram of that part of the preamplifier included inside the detector chamber (shown inside the dashed line in Fig. 1) is given in Fig. 2. The n-channel FET used (2N 3823) has a small input capacitance (6 pF max) and a high gm (3500 to 6500 µmhos) at zero bias and at room temperature. The optimum signal-to-noise performance of the FET was found to be at the temperature of approximately -130°C. Also, for optimum performance it is necessary to select the FET's. Another n-channel FET which gave slightly poorer performance was 2N3684.

วิทียที่ ทั้งสาราสิท ทั้ง จากสาราสาราส แต่ สิทิ หารไทยที่ 1+10 +00 โดย 10 สิโตโดย โดยให้สาริสาราส เป็น อย่าต

Further improvement of the signal-to-noise ratio of the charge-sensitive amplifier was achieved by filtering the output of the FET stage.

This is done by the integrator (0.1 µsec time constant) and by choosing low-f_T transistors for amplifier 1. The output signal of the charge-sensitive section is amplified by feedback amplifier 2 (gain of 10) in order to diminish the influence of low-frequency pickup by the cables between the preamplifier and the main amplifier.

The preamplifier performance was checked with pulse generator and radioactive sources. The conventional pulse generator test was carried out with a mercury-relay type RIDL pulse generator Model 47-3. An amount of charge simulating the γ -ray energies of 57 Co was inserted in the input of the FET through 0.5-pF capacitor, which was disconnected after the test. Noise line width of 0.7 keV FWHM was obtained with zero external capacitance when the FET was cooled to its optimum temperature.

The preamplifier assembly was checked for actual resolution with x rays of Pt and γ rays of 57 Co and 60 Co. The bias voltage for the detector was 1200 V, and the pulse-shaping time constants of the main amplifier were 0.5 µsec integration and 5 µsec differentiation. The pulse-height analyzer spectrum of Pt x rays and 57 Co γ rays is given in Fig. 3. The lines shown are K_{α} x rays (65.12 keV, 66.83 keV) and K_{β} x rays (75.75 keV, 77.87 keV) of platinum, and the γ rays (121.94 keV, 136.31 keV) of 57 Co. An expanded spectrum of the Pt x rays is shown in Fig. 4. From this spectrum the separation of the K_{α} group to K_{α_1} and K_{α_2} , which are only 1.71 keV apart, can be seen. Also the K_{β} group is resolved into K_{β_1} and K_{β_2} (2.12 keV apart). The resolution measured from Figs. 3 and 4 is 1.4 keV FWHM.

and with the pulse-shaping time constants. The resolution obtained for the γ rays (1.17 MeV and 1.33 MeV) of 60 Co was 5.7 keV. This degradation in resolution is due to the low efficiency of the detector (small size) for the high-energy γ rays.

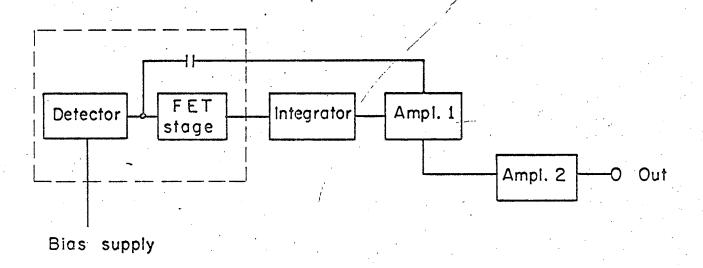
It is felt that the reported results can be improved beyond 1 keV by decreasing further the input capacitance of the preamplifier by using integrated circuit techniques with the FET and the detector deposited on the same wafer. Also, from comparing the pulse generator and analyzer resolutions, it can be seen that further decrease in the detector noise and capacitance will be welcomed.

Detailed description of the preamplifier and performance data will be published in the near future.

The author wishes to thank Michiyuki Nakamura for many helpful discussions, and David C. Camp and Guy A. Armantrout from the Livermore group for providing the germanium detector.

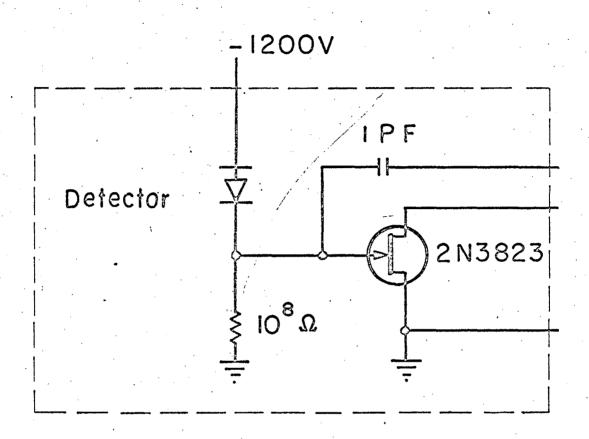
REFERENCES

- 1. V. Radeka, Brookhaven National Laboratory Report BNL-6953, 1963 (unpublished).
- 2. T. V. Blalock, IEEE Trans. on Nucl. Sci. NS-11 [3], 365 (1964).
- 3. T. W. Nybakken and V. Vali, Nucl. Instr. Meth. 32, 121 (1965).
- 4. G. A. Armantrout and D. C. Camp, Lawrence Radiation Laboratory
 Report UCRL-12333, 1965 (unpublished).



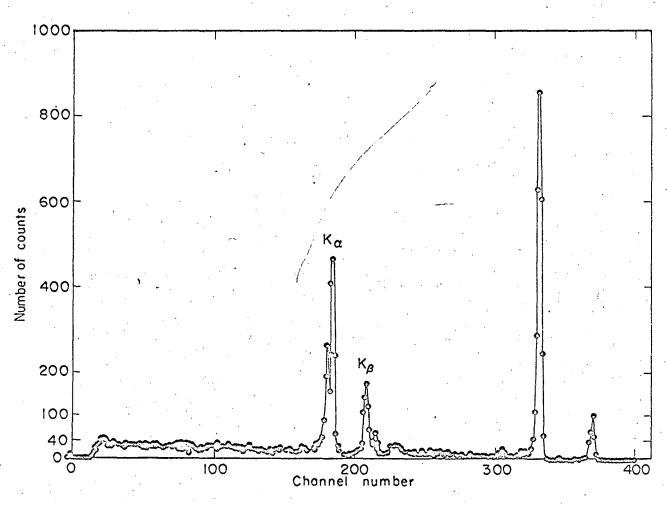
. MUB-7899

Fig. 1. Block diagram of the preamplifier.



MUB-7897

Fig. 2. The input stage of the preamplifier.



MUB-7898

Fig. 3. Platinum x rays and 57Co γ rays.

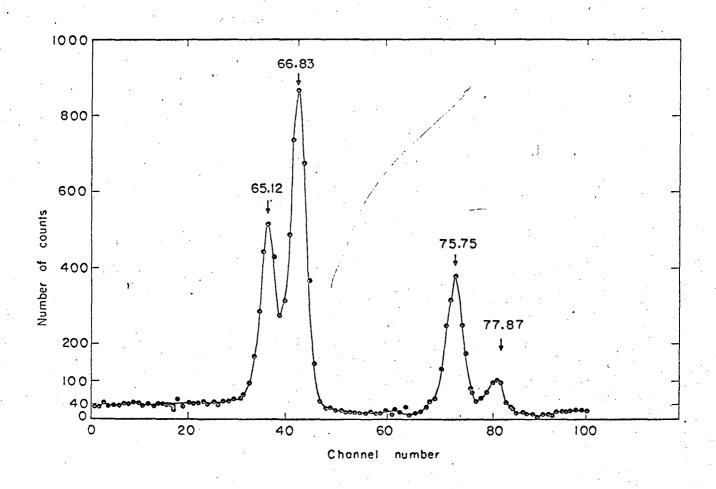


Fig. 4. K_{α} and K_{β} groups of platinum x rays.

This report was prepared as an account of Government sponsored work. Neither the United States, nor the Commission, nor any person acting on behalf of the Commission:

- A. Makes any warranty or representation, expressed or implied, with respect to the accuracy, completeness, or usefulness of the information contained in this report, or that the use of any information, apparatus, method, or process disclosed in this report may not infringe privately owned rights; or
- B. Assumes any liabilities with respect to the use of, or for damages resulting from the use of any information, apparatus, method, or process disclosed in this report.

As used in the above, "person acting on behalf of the Commission" includes any employee or contractor of the Commission, or employee of such contractor, to the extent that such employee or contractor of the Commission, or employee of such contractor prepares, disseminates, or provides access to, any information pursuant to his employment or contract with the Commission, or his employment with such contractor.

•